

## Features

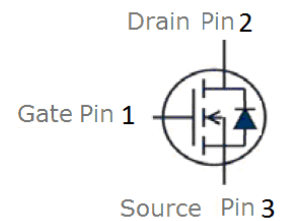
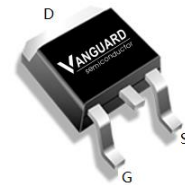
- Enhancement mode
- Low on-resistance  $R_{DS(on)}$  @  $V_{GS}=10\text{ V}$
- Fast Switching
- Pb-free lead plating; RoHS compliant



Part ID	Package Type	Marking	Tape and reel information
VS4N65CD	TO-252	4N65CD	2500pcs/Reel

$V_{DS}$	650	V
$R_{DS(on),TYP}$ @ $V_{GS}=10\text{ V}$	2.3	$\Omega$
$I_D$	4	A

### TO-252



## Maximum ratings, at $T_A = 25^\circ\text{C}$ , unless otherwise specified

Symbol	Parameter	Rating	Unit
$V_{(BR)DSS}$	Drain-Source breakdown voltage	650	V
$V_{GS}$	Gate-Source voltage	$\pm 30$	V
$I_S$	Diode continuous forward current	$T_C = 25^\circ\text{C}$ 4	A
$I_D$	Continuous drain current @ $V_{GS}=10\text{V}$	$T_C = 25^\circ\text{C}$ 4	A
		$T_C = 100^\circ\text{C}$ 2.5	A
$I_{DM}$	Pulse drain current tested ①	$T_C = 25^\circ\text{C}$ 16	A
$I_{DSM}$	Continuous drain current @ $V_{GS}=10\text{V}$	$T_A = 25^\circ\text{C}$ 0.5	A
		$T_A = 70^\circ\text{C}$ 0.4	A
EAS	Avalanche energy, single pulsed ②	144	mJ
$P_D$	Maximum power dissipation	$T_C = 25^\circ\text{C}$ 57	W
$P_{DSM}$	Maximum power dissipation ③	$T_A = 25^\circ\text{C}$ 1.25	W
$T_{STG}, T_J$	Storage and Junction Temperature Range	-55 to 150	$^\circ\text{C}$

## Thermal Characteristics

Symbol	Parameter	Typical	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	2.2	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	100	$^\circ\text{C/W}$

**Electrical Characteristics**

Symbol	Parameter	Condition	Min.	Typ.	Max.	Unit
<b>Static Electrical Characteristics @ T<sub>j</sub>=25°C (unless otherwise stated)</b>						
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	650	--	--	V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =650V, V <sub>GS</sub> =0V	--	--	1	μA
	Zero Gate Voltage Drain Current(T <sub>j</sub> =125°C)	V <sub>DS</sub> =520V, V <sub>GS</sub> =0V	--	--	50	μA
I <sub>GSS</sub>	Gate-Body Leakage Current	V <sub>GS</sub> =±30V, V <sub>DS</sub> =0V	--	--	±100	nA
V <sub>GS(TH)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	2.6	3.2	3.8	V
R <sub>DS(ON)</sub>	Drain-Source On-State Resistance <sup>④</sup>	V <sub>GS</sub> =10V, I <sub>D</sub> =2A	--	2.3	2.9	Ω
		T <sub>j</sub> =100°C	--	3.4	--	Ω
<b>Dynamic Electrical Characteristics @ T<sub>j</sub> = 25°C (unless otherwise stated)</b>						
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V, f=1MHz	420	495	570	pF
C <sub>oss</sub>	Output Capacitance		30	45	60	pF
C <sub>rss</sub>	Reverse Transfer Capacitance		--	7	20	pF
R <sub>g</sub>	Gate Resistance	f=1MHz	--	1.8	--	Ω
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> =320V, I <sub>D</sub> =4A, V <sub>GS</sub> =10V	--	15.2	--	nC
Q <sub>gs</sub>	Gate-Source Charge		--	3.6	--	nC
Q <sub>gd</sub>	Gate-Drain Charge		--	3.4	--	nC
<b>Switching Characteristics</b>						
t <sub>d(on)</sub>	Turn-on Delay Time	V <sub>DD</sub> =320V, I <sub>D</sub> =4A, R <sub>G</sub> =10Ω, V <sub>GS</sub> =10V	--	7.8	--	ns
t <sub>r</sub>	Turn-on Rise Time		--	7	--	ns
t <sub>d(off)</sub>	Turn-Off Delay Time		--	18	--	ns
t <sub>f</sub>	Turn-Off Fall Time		--	27	--	ns
<b>Source- Drain Diode Characteristics @ T<sub>j</sub> = 25°C (unless otherwise stated)</b>						
V <sub>SD</sub>	Forward on voltage	I <sub>SD</sub> =4A, V <sub>GS</sub> =0V	--	0.9	1.2	V
t <sub>rr</sub>	Reverse Recovery Time	T <sub>j</sub> =25°C, I <sub>sd</sub> =4A, V <sub>GS</sub> =0V	--	398	--	ns
Q <sub>rr</sub>	Reverse Recovery Charge	di/dt=100A/μs	--	1.5	--	uC

NOTE:

- ① Repetitive rating; pulse width limited by max junction temperature.
- ② Limited by T<sub>Jmax</sub>, starting T<sub>J</sub> = 25°C, L = 18mH, R<sub>G</sub> = 25Ω, I<sub>AS</sub> = 4A, V<sub>GS</sub> = 10V. Part not recommended for use above this value
- ③ The power dissipation P<sub>DSM</sub> is based on R<sub>θJA</sub> and the maximum allowed junction temperature of 150°C.
- ④ Pulse width ≤ 300μs; duty cycle ≤ 2%.

Typical Characteristics

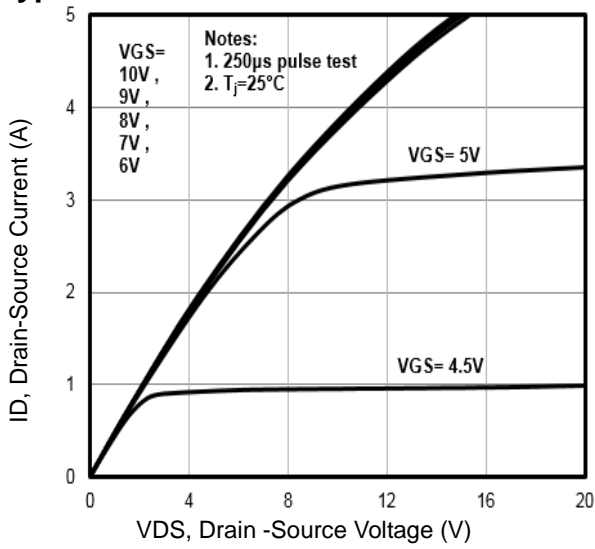


Fig1. Typical Output Characteristics

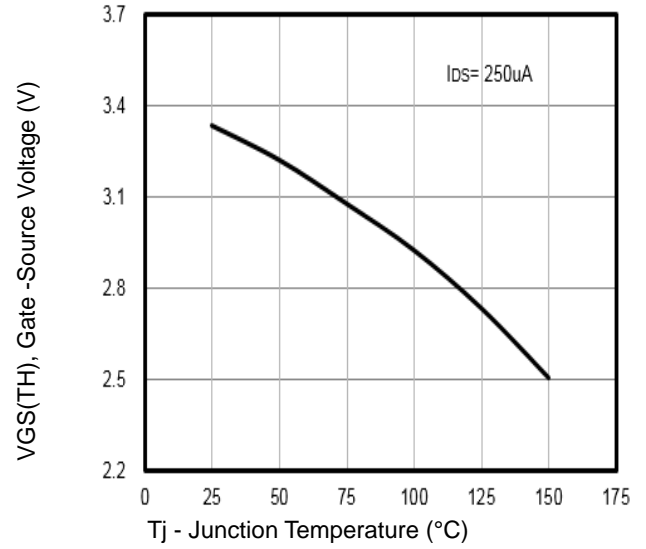


Fig2.  $V_{GS(TH)}$  Gate-Source Voltage Vs.  $T_j$

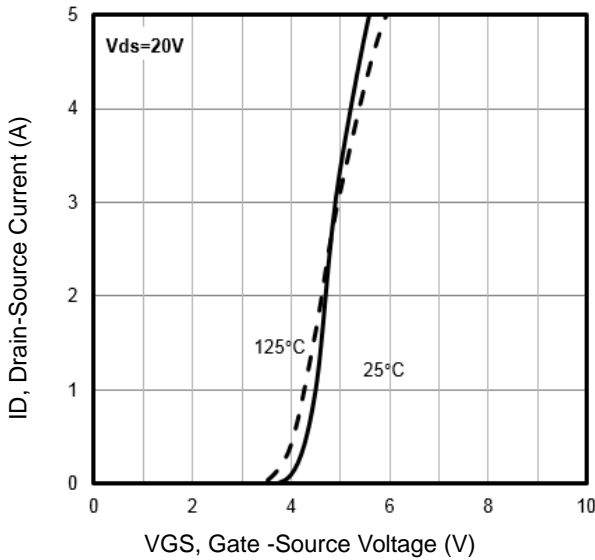


Fig3. Typical Transfer Characteristics

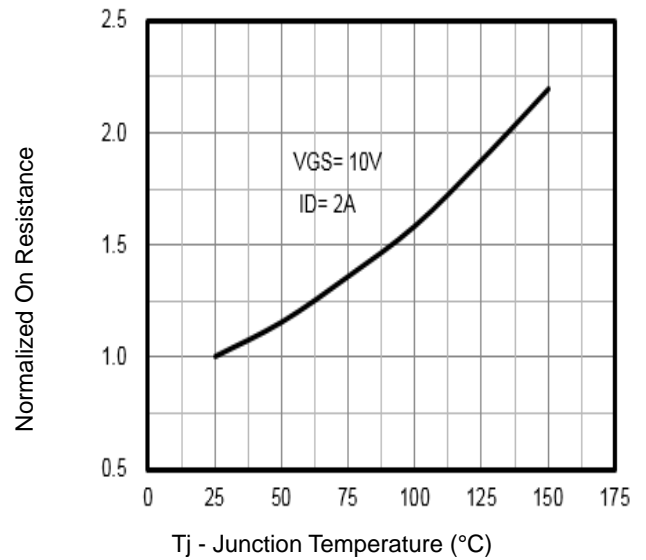


Fig4. Normalized On-Resistance Vs.  $T_j$

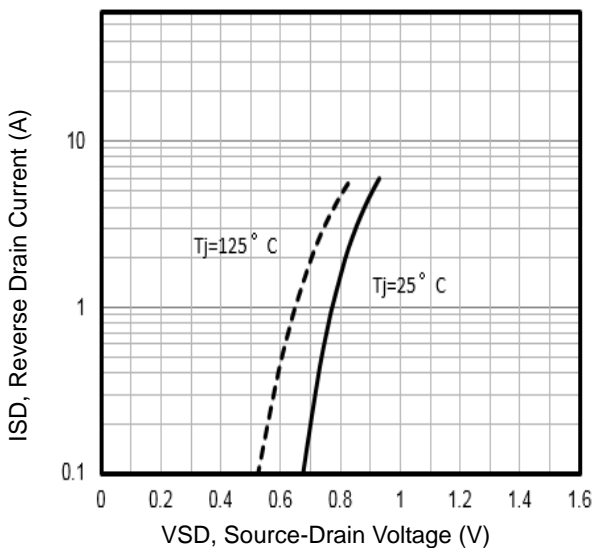


Fig5. Typical Source-Drain Diode Forward Voltage

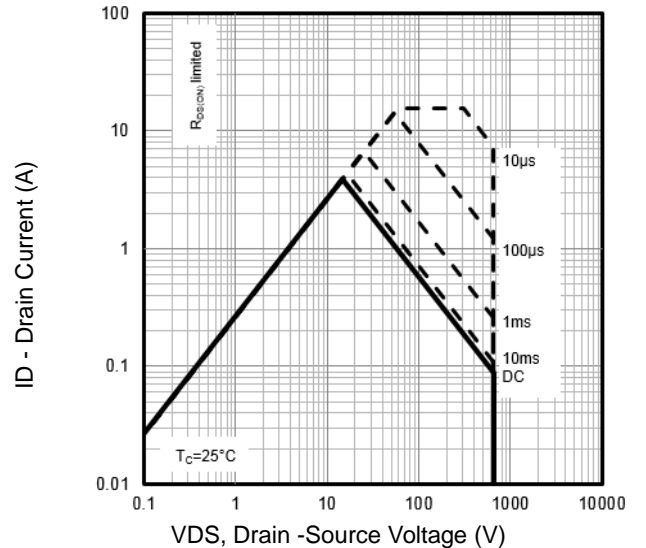


Fig6. Maximum Safe Operating Area

Typical Characteristics

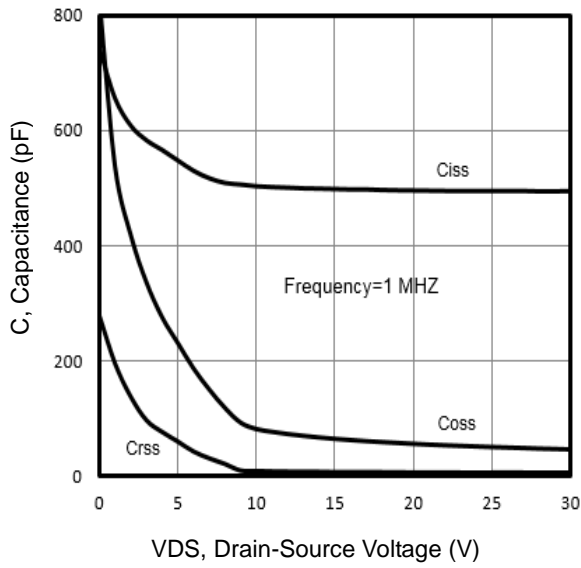


Fig7. Typical Capacitance Vs. Drain-Source Voltage

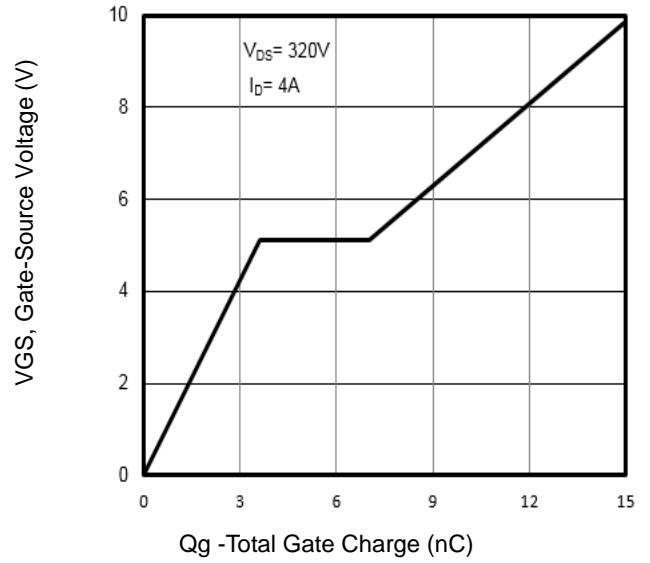


Fig8. Typical Gate Charge Vs. Gate-Source Voltage

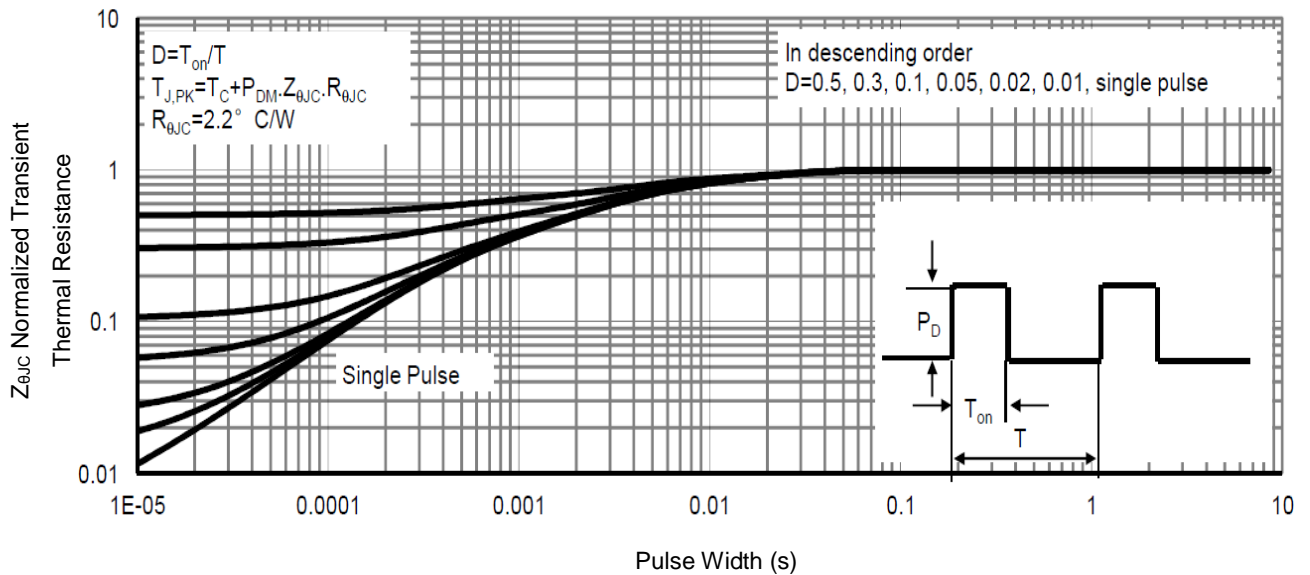


Fig9. Normalized Maximum Transient Thermal Impedance

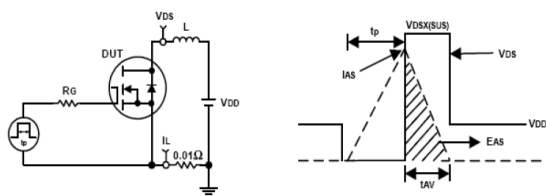


Fig10. Unclamped Inductive Test Circuit and waveforms

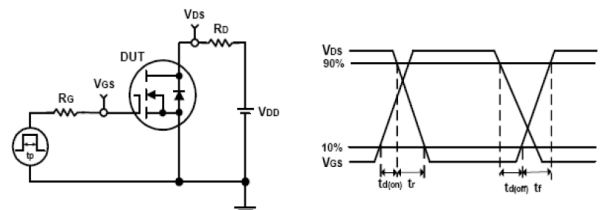
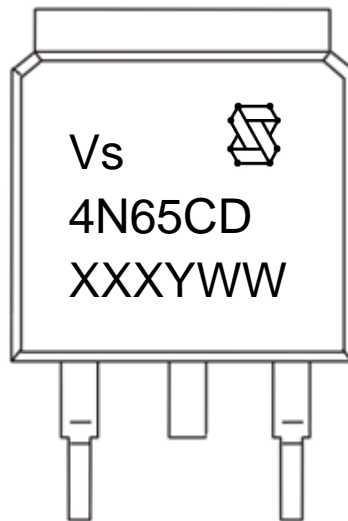


Fig11. Switching Time Test Circuit and waveforms

### Marking Information



1st line: Vanguard Code (Vs), Vanguard Logo

2nd line: Part Number (4N65CD)

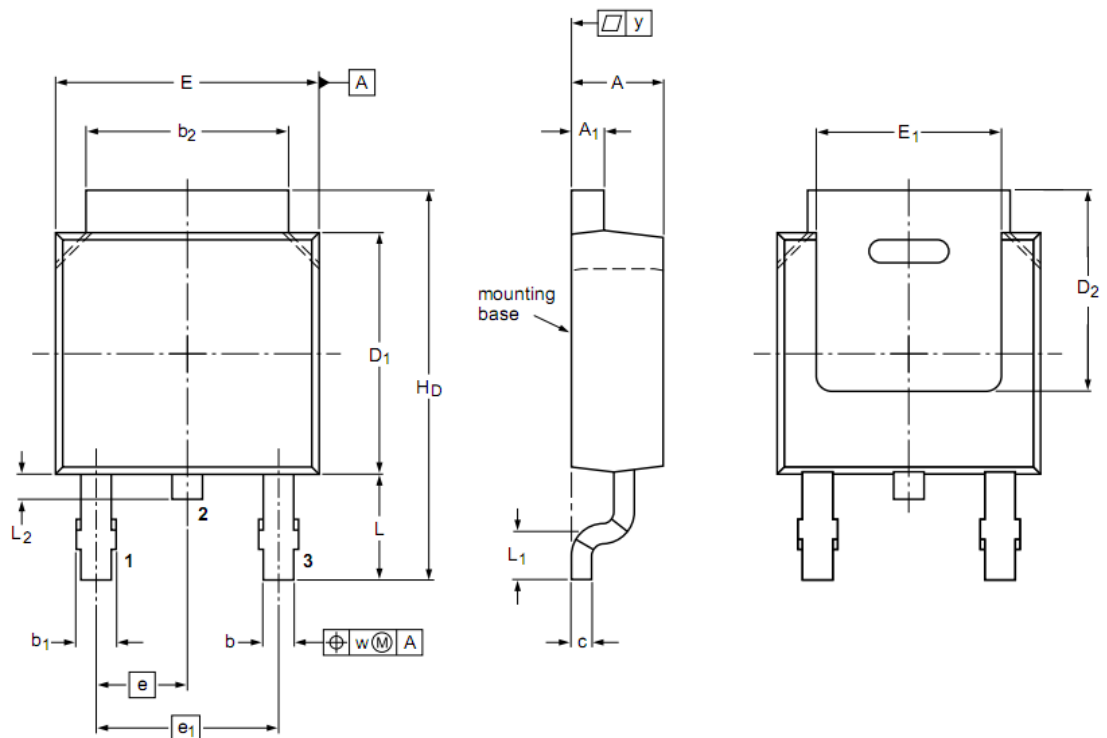
3rd line: Date code (XXXYWW)

XXX: Wafer Lot Number Code , code changed with Lot Number

Y: Year Code, (e.g. E=2017, F=2018, G=2019, H=2020, etc)

WW: Week Code (01 to 53)

### TO-252 Package Outline Data



Symbol	Dimensions (unit: mm)		
	Min	Typ	Max
A	2.20	2.30	2.38
A <sub>1</sub>	0.46	0.50	0.63
b	0.64	0.76	0.89
b <sub>1</sub>	0.77	0.85	1.14
b <sub>2</sub>	5.00	5.33	5.46
c	0.458	0.508	0.558
D <sub>1</sub>	5.98	6.10	6.223
D <sub>2</sub>	5.21	--	--
E	6.40	6.60	6.731
E <sub>1</sub>	4.40	--	--
e	2.286 BSC		
e <sub>1</sub>	--	4.57	--
H <sub>D</sub>	9.40	10.00	10.40
L	2.743 REF		
L <sub>1</sub>	1.40	1.52	1.77
L <sub>2</sub>	0.50	0.80	1.01
w	--	0.20	--
y	--	--	0.20

#### Notes:

1. Refer to JEDEC TO-252 variation AA
2. Dimension "E" does NOT include mold flash, protrusions or gate burrs. Mold flash, protrusions or gate burrs shall not exceed 0.1524mm per side.
3. Dimension "D1" does NOT include interlead flash or protrusion. Interlead flash or protrusion shall not exceed 0.1524mm per end.

### Customer Service

#### Sales and Service:

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